

APR 14 2003

15.55/6364

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of) Examiner: T. L. Dickey
EBINA)
Serial No.: 10/050,793) Art Unit: 2826
Filing Date: January 18, 2002)
For: SEMICONDUCTOR DEVICES)
AND METHODS FOR)
MANUFACTURING THE SAME) AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sirs:

In response to the Office Action dated December 4, 2002 in the above-referenced application, response to which is due April 4, 2003 with a one-month extension of time (petition for which is attached hereto), please enter and consider the following amendments and remarks:

IN THE FIGURES:

Applicant proposes to amend Fig. 2 as shown in red on the attached sheet.

IN THE CLAIMS:

Please cancel claims 16-22 without prejudice.

Please amend claims 1-2, 4, 6-7 and 9-14 as follows:

1. (Amended) A semiconductor device comprising:
an insulation layer;
a semiconductor layer formed on the insulation layer;
an element isolation region formed in the semiconductor layer; and
a first element forming region and a second element forming region defined by the
element isolation region;
wherein the first element forming region includes both a first bi-polar transistor and a first
field effect transistor;

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